## The stopping distribution of low energy  ${}^{8}$ Li<sup>+</sup>

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(Dated: April 2004)

This is meant to be an introduction to this important aspect of using  $\beta$ -NMR as a depth-resolved magnetic probe. What do we know about the stopping distribution of Li? Why do we need to know the stopping distribution? How to use the stopping distribution? Disclaimer: Just because it's nicely typeset doesn't mean it's error-free.

PACS numbers:

## I. THE IMPORTANCE

To make the depth profiling capability of  $\beta$ -NMR quantitative, it is essential to have a complete understanding of the stopping distribution of the probe,  ${}^{8}$ Li<sup>+</sup> (with kinetic energy 10 eV - 30 keV). For example, Fig.2 shows the bias scan of the  $\beta$ -NMR resonances at 280 K in the epitaxial heterostructure GaAs $\langle 100 \rangle$  20Å Fe/ 800 Å Ag  $40$  Å Au. At intermediate bias, the stopping distribution might be qualitatively as shown in Fig.1. In order to get a meaningful fit of the resonance at the Larmor frequency, it is important to know how much of this resonance could be due to <sup>8</sup>Li stopping in the substrate, for example. Even if all the  ${}^{8}$ Li stops in the Ag layer, the implantation depth profile will cause a nonuniform sampling of any depth dependant phenomena in the Ag layer.

A great deal is known about the stopping of ions in matter<sup>1,2</sup>, primarily because ion beam irradiation is a technique used in industrial semiconductor manufacturing, however, the energies we are interested in are typically much lower than those that have been studied.



FIG. 1: A to-scale representation of the thin-iron thick-silver heterostructure with a representative gaussian stopping distribution superposed. The heterostructure is a capping layer of 20 monolayers of Au on 400 ML of Ag on 14 ML of Fe on the GaAs substrate.



FIG. 2: Platform bias scan of the resonances of <sup>8</sup>Li in the heterostructure shown in Fig. 1. Figure courtesy of A.N. Macdonald and T.A. Keeler.

Monte carlo computer programs to model the stopping of ions have been developed and extensively compared with experiments. Experiments implanting radioactive probes are one such test, but also one can depth profile implanted ions using techniques like SIMS and Auger Spectroscopy in combination with a sputter gun (for holedigging). One such program is SRIM<sup>3</sup>. This appears to be an offshoot of an original program called TRIM. We are currently using a modified version of TRIM, called TRIM.SP (modified by  $LE\mu SR<sup>4</sup>$ ). These programs typically do not include the effects of channeling which can have significant effects on the stopping distribution in crystalline films. They do include density and nuclear charge (atomic number Z) effects, but no microstructural effects of the lattice. The output of such programs



FIG. 3: Predicted stopping distributions from TRIM.SP for various <sup>8</sup>Li energies (points) and beta distribution fits (lines) (Courtesy D. Wang).

is a set of points scattered about a theoretical stopping distribution. Presumably with enough simulations these points would converge on a smooth curve. The physical processes important in stopping ions are given in refs<sup>1,2</sup>. Zaher has agreed to show us how to operate TRIM.SP sometime in the near future.

One question immediately arises, what is a good phenomenological functional form for the stopping distribution? If we can find a nice parametrization of the predicted distribution, then we could use it to sort out examples, such as the above, in a convenient way. I will show some examples of this in the next section. Typically the stopping distribution is approximated as a gaussian, but often the distribution is not that symmetric, particularly when there is a channeling peak which can make the distribution bimodal.

As an example, Dong Wang finds the stopping distribution for  ${}^{8}$ Li in NbSe<sub>2</sub> is not well-described by a gaussian and has parametrized it instead using the beta distribution:

$$
f(z; a, b) = \begin{cases} c \frac{\Gamma(a+b)}{\Gamma(a)\Gamma(b)} \tilde{z}^{a-1} (1-\tilde{z})^{b-1}, & \text{for } z \in (0,1) \\ 0, & \text{elsewhere,} \end{cases}
$$
 (1)

where  $\tilde{z} = z/z_0$  is a dimensionless normalized depth. This distribution has a mean value  $a/(a + b)$  and a variance  $ab/(1+b)^2(a+b+1)^5$ . The fits to the monte carlo data for  ${}^{8}$ Li stopping in NbSe<sub>2</sub> are shown in Fig.(3). One can see that the fits are quite reasonable. To my knowledge, there is nothing fundamental in the use of the beta distribution, it is just a versatile phenomoenological form. Another question that this suggests: is there a natural function to use (beyond the gaussian)?

The monte carlo programs involve phenomenological parameters which can be adjusted to match experiment. Some work has been done using  ${}^{7}$ Li in Si for example<sup>6</sup>, but for our energy range, it may also be necessary to more extensively test the predictions of such programs using  $\beta$ -NMR (along the lines of refs<sup>4,7</sup>) and possibly have the programs modified if necessary.

Once we've established the stopping distribution, we can use it.

TABLE I: Beta Distribution fits to the TRIM.SP implantation distributions predicted for NbSe2, courtesy D. Wang.

| z <sub>0</sub> | a          | b          | c          |
|----------------|------------|------------|------------|
| 36.6345566     | 2.26532368 | 9.99987784 | 531.450668 |
| 44.4667757     | 1.97723688 | 5.46752944 | 464.461677 |
| 61.2272566     | 1.91213954 | 4.97494402 | 348.940872 |
| 75.2823165     | 1.93321953 | 4.70395483 | 287.640109 |
| 92.7180259     | 1.98794684 | 4.8315186  | 233.83368  |
| 98.9102647     | 1.89046751 | 4.04500465 | 225.227106 |
| 112.820278     | 1.90773033 | 3.94678169 | 201.181766 |
| 123.054994     | 1.84876239 | 3.57720408 | 183.514615 |
| 137.737008     | 1.90512292 | 3.70553565 | 166.68641  |
| 150.876939     | 1.97880687 | 3.71901639 | 152.976878 |
| 163.490127     | 1.85160299 | 3.48256345 | 143.172482 |
| 170.094569     | 1.82135816 | 3.23726676 | 138.365966 |
| 182.149078     | 1.89645047 | 3.23671691 | 130.017247 |
| 191.204039     | 1.8776904  | 3.05018485 | 123.831776 |
| 201.694888     | 1.83905356 | 2.95049773 | 117.745477 |
| 225.233111     | 1.90639674 | 3.33449463 | 107.329452 |
| 228.421776     | 1.87057812 | 2.96861776 | 105.892253 |
| 243.01845      | 1.83103418 | 2.96221407 | 99.5099627 |
| 249.477327     | 1.88240882 | 2.91134987 | 98.2316292 |
| 263.418696     | 1.90163948 | 2.93438484 | 93.0507106 |
| 285.633692     | 1.97929866 | 3.20047128 | 85.9414003 |
| 287.856909     | 1.88492041 | 2.86652492 | 85.8899272 |
| 292.712885     | 1.85466977 | 2.6978884  | 84.912697  |
| 300.477411     | 1.89351582 | 2.67740833 | 83.0602773 |
| 313.840519     | 1.89672577 | 2.65922732 | 79.4092317 |
| 310.8078       | 1.86468413 | 2.42863878 | 81.0833696 |
| 321.232072     | 1.85498209 | 2.4108844  | 77.6549641 |
| 314.4151       | 1.80269017 | 2.16417479 | 79.2862474 |
| 316.517473     | 1.78742292 | 2.05951497 | 78.6042134 |
| 321.381984     | 1.75507736 | 2.03051767 | 77.5070534 |

## II. USING THE STOPPING DISTRIBUTION

Here I develop some general calculations for using the stopping distribution. The first is to calculate a field distribution in a nonuniform field situation. A particularly simple (yet interesting) instance of this is the Meissner phase of a superconductor.

For a superconductor in the Meissner Phase, the magnetic field falls as  $B_0e^{-\alpha z}$  away from the surface, where  $\alpha = 1/\lambda$ . First let's assume a completely uniform stopping distribution for <sup>8</sup>Li, i.e. the probability density of finding <sup>8</sup>Li at depth  $z(\mathcal{P}(z))$  is just  $1/d$  up to the maximum implantation depth d. We will see how to relax this assumption in a moment. First, what should the field distribution function  $(P(B))$  look like qualitatively? The maximum field is clearly  $B_0$  and the minimum is  $B_0e^{-\alpha d}$ . Many more z values correspond to fields near the minimum field, so we expect  $P(B)$  to be a maximum



FIG. 4: The field distributions for a uniformly distributed probe in the Meissner state of a superconductor in a magnetic field  $B_0$  smaller than the critical fields for a range of ratios of the maximum implantation depth relative  $d$  relative to the penetration depth  $\lambda$ .

there. One can calculate  $P(B)$  in the following way<sup>8</sup>:

$$
P(B) = N \int_0^\infty \mathcal{P}(z) dz \delta(B - B(z)) \tag{2}
$$

$$
= \frac{N}{d} \int_0^d dz \delta(B - B(z)), \tag{3}
$$

where N is a factor ensuring normalization of  $P(B)$ . Using the well-known property of the Dirac delta function:

$$
\delta(f(z)) = \sum_{i} \frac{\delta(z - z_i)}{\left|\frac{df}{dz}\right|_{z_i}},\tag{4}
$$

where  $z_i$  are the i distinct zeros of f, we get

$$
P(B) = \frac{N}{d} \int_0^d dz \frac{\delta(z - z_1)}{|-\alpha B_0 e^{-\alpha z_1}|},\tag{5}
$$

where  $z_1 = -\lambda \ln (B/B_0)$  is the only zero of  $\delta$ 's argument. From this,

$$
P(B) = \begin{cases} \frac{N}{d\alpha B} & \text{for } z_1 \in [0, d] \\ 0 & \text{elsewhere,} \end{cases}
$$
 (6)

or equivalently,

$$
P(B) = \begin{cases} \frac{N}{d\alpha B} & \text{for } B \in [B_0 e^{-\alpha d}, B_0] \\ 0 & \text{elsewhere.} \end{cases}
$$
(7)

One can use the normalization condition,  $\int P(B)dB = 1$ to find that  $N = 1$ . Fig. 4 shows  $P(B)$  for variety of  $d/\lambda$ values. Clearly from the form of  $P(B)$  if the implantation depth is infinite,  $P(B)$  becomes infinitely peaked at  $B =$ 0.



FIG. 5: An example of the (truncated) gaussian stopping distribution (properly normalized) to the normalized magnetic field profile.

Lets try a more realistic <sup>8</sup>Li stopping distribution  $P(z)$ like a gaussian,

$$
\mathcal{P}(z) = A \exp(-(z - z_0)^2 / 2r^2),\tag{8}
$$

where  $A$  is a normalization factor,  $z_0$  is the most probable stopping depth and  $r$  is a measure of the range straggling. Fig. 5 shows an example of this stopping distribution together with the spatial dependence of the magnetic field. Now we can proceed to calculate the field distribution.

$$
P(B) = N \int_0^\infty \mathcal{P}(z) dz \delta(B - B(z)) \tag{9}
$$

$$
= NA \int_0^\infty dz e^{-\frac{(z-z_0)^2}{2r^2}} \delta(B - B(z)) \qquad (10)
$$

$$
= NA \int_0^\infty dz e^{-\frac{(z-z_0)^2}{2r^2}} \frac{\delta(z-z_1)}{|-\alpha B_0 e^{-\alpha z_1}|} \quad (11)
$$
  

$$
e^{-\frac{(\lambda \ln(B_0) + z_0)^2}{2r^2}}
$$
 (13)

$$
= NA \frac{e^{-2r^2}}{\alpha B}, \qquad (12)
$$

for  $B \in (0, B_0]$ . Note A has units of 1/length, so P has units of 1/field and N is unitless. Note that as  $B \to 0$ , the singular behaviour (for  $d \to \infty$ ) we had with the uniform stopping distribution is now cut off by the gaussian in the numerator, and we can take the integral to  $z \to \infty$ .

For the sake of plotting this distribution, let's assume that the straggling  $r = 0.8z_0$  (typical). Fig. 6 shows the resulting distribution  $P(B)$  for a range of values of  $z_0/\lambda$ . To compare this with Fig. 4, use  $z_0 \approx d/2$ . Note there is still a sharp cutoff in  $P(B)$  at the high field side, corresponding to the finite value of  $\mathcal{P}(z)$  at the surface, i.e. the depth of maximal field  $B_0$ .

This particular example may be relevant for low field studies in superconductors similar to what has been done with  $LE\mu$ SR<sup>9</sup>, where B could be the static field or the RF field  $B_1$ . For the LE muons, the stopping distribution was



FIG. 6: The field distributions for a gaussian distributed probe in the Meissner state of a superconductor in a magnetic field  $B_0$  smaller than the critical fields for a range of ratios of the maximum of  $P(z)$ , the most probable implantation depth,  $z_0$  relative to the penetration depth  $\lambda$ . The range straggling r is a fixed fraction 0.8 of  $z_0$ .

- <sup>1</sup> e.g. see the textbook: Ion Implantation, Sputtering and their Applications by P.D. Townsend, J.C. Kelly and N.E.W. Hartley (Academic, NY, 1976).
- <sup>2</sup> Ion Implantation Science and Technology J.F. Ziegler ed. (Academic, NY, 1988).
- $3 \text{ http://www.srim.org/}$
- $^{4}$  E. Morenzoni et al., NIMB 192, 254 (2002).
- <sup>5</sup> P.C. Gregory, book on Bayesian Statistics, used for Phys509

taken directly from TRIM.SP without parametrization, see Fig. 2 of Ref.<sup>9</sup> and note the absence of scatter. This approach is certainly more general purpose than trying to parametrize the results of TRIM.SP. But either way, we rely on the correctness of the monte carlo simulations. I hope this introduction helps us to focus on the relevance of the stopping distribution and motivates progress in this direction.

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- $6$  D.L. da Silva et al. NIMB 175-177, 98 (2001).
- <sup>7</sup> T.R. Beals *et al.* Physica B **326**, 205 (2003).
- <sup>8</sup> There are other ways to do this, see the "Density of Levels" discussion in Chapter 8 of Ashcroft and Mermin.
- $9$  T.J. Jackson et al., Phys. Rev. Lett. 84, 4958-4961 (2000).